Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H1836

■ FOR HIGH VOLTAGE AMPLIFIER APPLICATIONS

PLASMA DISPLAY，NIXIE TUBE DRIVER APPLICATIONS.

COLOR TV VIDEO OUTPUT APPLICATIONS.

■ ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… -55~150℃

T_j——Junction Temperature……150℃

P_C——Collector Dissipation……625mW

V_{CBO}——Collector-Base Voltage……300V

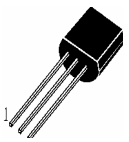
V_{CEO}——Collector-Emitter Voltage……300V

V_{EBO}——Emitter-Base Voltage……6V

I_C——Collector Current……100mA

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TO-92



1－Emitter，E
2－Base，B
3－Collector，C

■ ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	300			V	I_C=100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	300			V	I_C=1mA, I_B=0
I_{CBO}	Collector Cut-off Current			0.1	μA	V_{CB}=300V, I_E=0
I_{EBO}	Emitter Cut-off Current			0.1	μA	V_{EB}=6V, I_C=0
H_{FE}（1）	DC Current Gain	20				V_{CE}=10V, I_C=1mA
H_{FE}（1）		30		150		V_{CE}=10V, I_C=20mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.5	V	I_C=20mA, I_B=2mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			1.2	V	I_C=20mA, I_B=2mA
f_T	Current Gain-Bandwidth Product	50	80		MHz	V_{CE}=10V, I_C=20mA
Cob	Output Capacitance		3	4	pF	V_{CB}=20V, I_E=0，f=1MHz